

Features

- ◆ Transient protection for data lines to
IEC 61000-4-2 (ESD) $\pm 30\text{kV}$ (air), $\pm 30\text{kV}$ (contact)
IEC 61000-4-4 (EFT) 40A (tp = 5/50ns)
Cable Discharge Event (CDE)
- ◆ Ultra-small package (1.0 x 0.6 x 0.5mm)
- ◆ Protects one data or I/O line
- ◆ Low capacitance: **0.35pF**
- ◆ Low clamping voltage
- ◆ Low operating voltage: 5.0V
- ◆ Solid-state silicon-avalanche technology

Mechanical Characteristics

- ◆ Package: DFN1006-2 (0402)
- ◆ Lead Finish: Matte Tin
- ◆ UL Flammability Classification Rating 94V-0
- ◆ Pb-Free, Halogen Free, RoHS/WEEE Compliant

RoHS



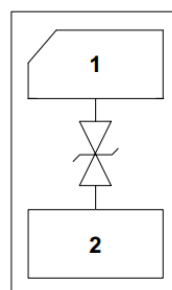
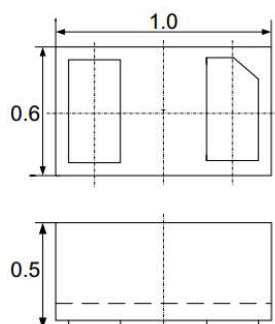
Applications

- ◆ Cellular Handsets & Accessories
- ◆ Digital Visual Interface (DVI)
- ◆ Display Port
- ◆ MDDI Ports
- ◆ USB Ports
- ◆ PCI Express
- ◆ Serial ATA

Ordering Information

Part Number	Qty per Reel	Reel Size
TPESD0531T	3000	7"

Dimensions and Pin Configuration

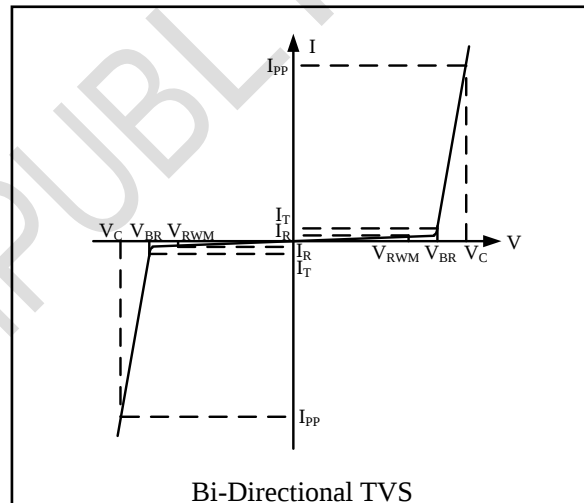


Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20 μs)	P_{pk}	80	W
ESD per IEC61000-4-2 (Air)	V_{ESD}	± 30	kV
ESD per IEC61000-4-2 (Contact)		± 30	
Operating Temperature Range	T_J	-55 to +150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter
V_{RWM}	Nominal Reverse Working Voltage
I_R	Reverse Leakage Current @ V_{RWM}
V_{BR}	Reverse Breakdown Voltage @ I_T
I_T	Test Current for Reverse Breakdown
V_C	Clamping Voltage @ I_{pp}
I_{pp}	Maximum Peak Pulse Current
C_{ESD}	Parasitic Capacitance
V_R	Reverse Voltage
f	Small Signal Frequency



Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V_{RWM}			5	V	
Breakdown Voltage	V_{BR}	6			V	$I_T = 1\text{mA}$
Reverse Leakage Current	I_R			0.3	μA	$V_{RWM} = 5\text{V}$
Clamping Voltage	V_C			15	V	$I_{PP} = 1\text{A}$ (8 x 20 μs pulse)
Clamping Voltage	V_C			24	V	$I_{PP} = 4.5\text{A}$ (8 x 20 μs pulse)
Junction Capacitance	C_J		0.35	0.5	pF	$V_R = 0\text{V}$, $f = 1\text{MHz}$

Typical Performance Characteristics ($T_A=25^\circ\text{C}$ unless otherwise Specified)

Fig1. 8/20 μs Pulse Waveform

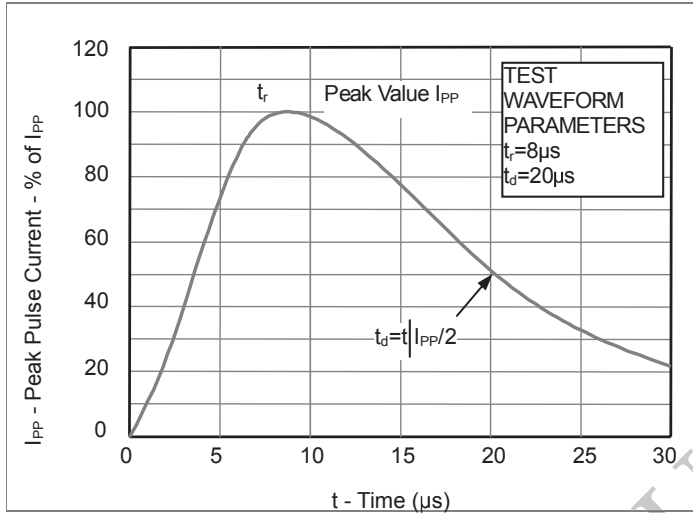


Fig2. ESD Pulse Waveform (according to IEC 61000-4-2)

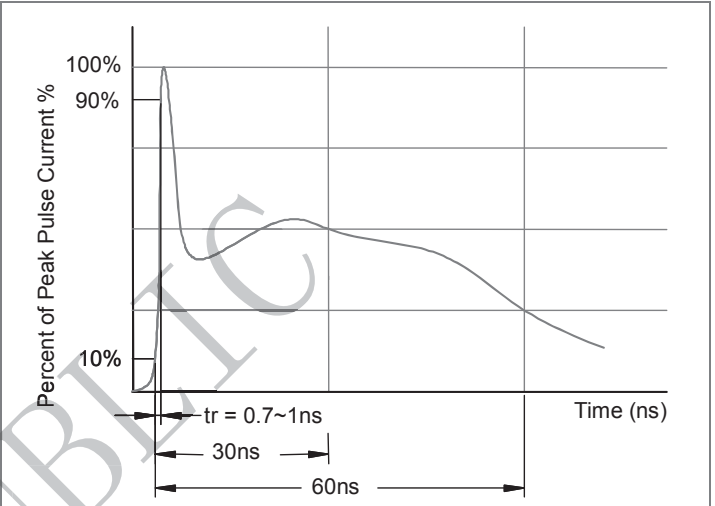
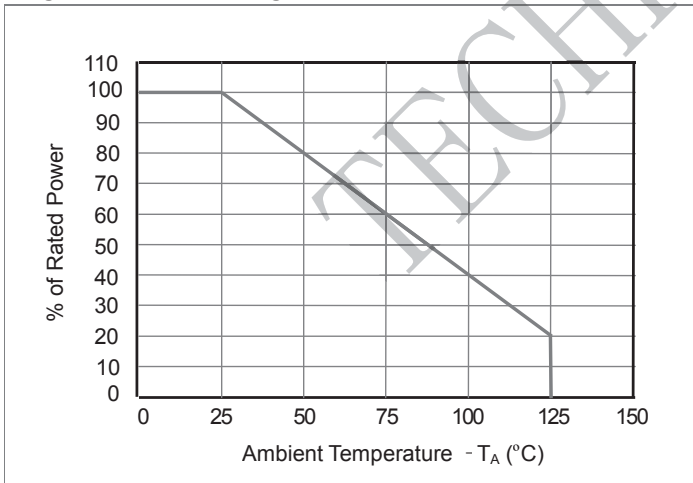
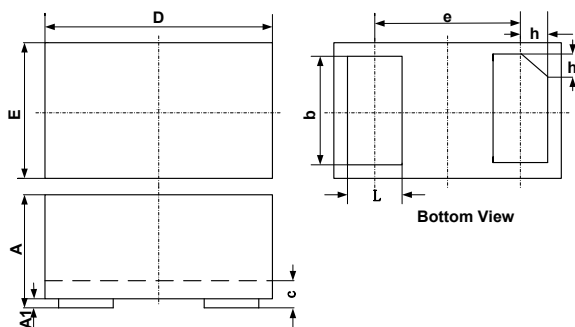


Fig3. Power Derating Curve

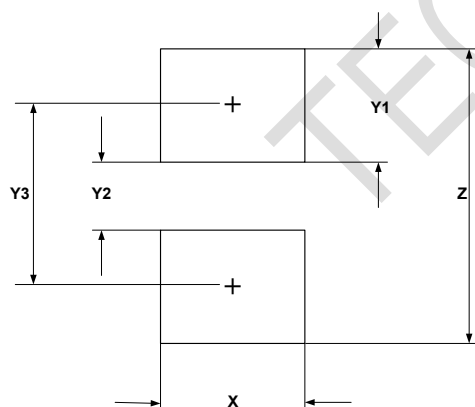


Outline Drawing - DFN1006-2



SYM	DIMENSIONS					
	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.45	0.50	0.55	0.018	0.020	0.022
A1	0.00	0.02	0.05	0.000	0.001	0.002
b	0.45	0.50	0.55	0.018	0.020	0.022
c	0.12	0.15	0.18	0.005	0.006	0.007
D	0.95	1.00	1.05	0.037	0.039	0.041
e	0.65 BSC			0.026 BSC		
E	0.55	0.60	0.65	0.022	0.024	0.026
L	0.20	0.25	0.30	0.008	0.010	0.012
h	0.07	0.12	0.17	0.003	0.005	0.007

Land Pattern - DFN1006-2



SYM	DIMENSIONS	
	MILLIMETERS	INCHES
X	0.60	0.024
Y1	0.50	0.020
Y2	0.30	0.012
Y3	0.80	0.032
Z	1.30	0.052